

8 High voltage fast recovery diode for snubber circuit (Non-insulated)

Device type	V_{RRM} Volts	V_{RSM} Volts	$I_{F(AV)}$ Amps.	I_{FSM} Amps.	I^2t A ² s	V_{FM} Volts	I_{RRM} mA	t_{rr} μ s	$R_{th(j-c)}$ °C/W	Package	Net weight Grams
ERG28-12	1200	1320	30	500	1000	3.0	10	0.60	0.80	—	25
ERG78-12	1200	1320	30	500	1000	3.0	10	0.60	0.80	—	25
1F60A-120F	1200	1320	60	1000	4000	3.0	20	0.60	0.32	R101	33
1F60A-120R	1200	1320	60	1000	4000	3.0	20	0.60	0.32	R101	33

9 Schottky-barrier diode modules

Device type	V_{RRM} Volts	V_{RSM} Volts	$I_{F(AV)}$ Amps.	I_{FSM} Amps.	I^2t A ² s	V_{FM} Volts	I_{RRM} mA	$R_{th(j-c)}$ °C/W	Package	Net weight Grams	Internal circuit
2BI60E-004	40	48	60 × 2	850	2890	0.58	300	0.5	R205A	110	Fig. 5
2BI100E-004	40	48	100 × 2	1600	10240	0.55	600	0.3	R205A	110	Fig. 5
2BI200E-004C, N, D	40	48	200 × 2 *	3000	36000	0.55	1200	0.15	R208	150	Fig. 5

* I_o **10 Diode and thyristor modules**

Device type	Application	Diode and thyristor						Diode	Thyristor		Package	Net weight Grams	Internal circuit
		V_{RRM} Volts	V_{RSM} Volts	$I_{O(AV)}$ Amps.	I_{TSM} Amps.	I^2t A ² s	T_j °C	V_{FM} Volts	V_{TM} Volts	I_{GT} mA			
3R3TI20E-080	Power supply for inverter, battery charger and DC motor	800	900	20	400	660	125	Rectifier: 1.20	1.30	80	R611	140	Fig. 6
3R3TI30E-080		800	900	30	600	1490	125		1.40	80	R611	140	Fig. 6
3R3TI60E-080		800	900	60	1000	4150	125		1.30	80	R611	140	Fig. 6
4R3TI20Y-080		800	900	20	400	660	125	Rectifier: 1.20	1.30	80	R701	140	Fig. 7
4R3TI30Y-080		800	900	30	600	1490	125		1.40	80	R701	140	Fig. 7
4R3TI60Y-080		800	900	60	1000	4150	125	Output: 1.10	1.30	80	R701	140	Fig. 7
6R1TI30Y-080	For dynamic breaking circuit	800	900	30	300	375	125		1.40	80	R702	140	Fig. 8

Internal circuit

Fig.1

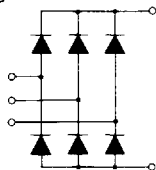


Fig.2



Fig.3

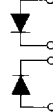


Fig.4

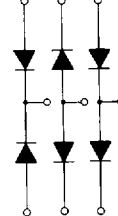


Fig.5

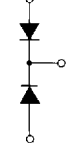


Fig.6

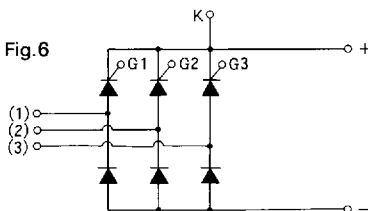


Fig.7

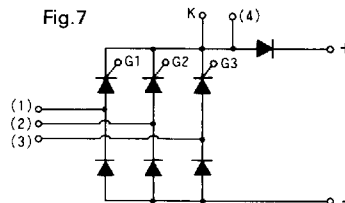


Fig.8

